

L Number	Hits	Search Text	DB	Time stamp
-	21	"3943462"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:08
-	0	(semiconductor adj laser) and facet and (anti\$reflection adj coating) and (thickness adj3 quarter) and sion\$h and pecvd and (optical adj index)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:17
-	0	(semiconductor adj laser) and facet and (antireflection adj coating) and (thickness adj3 quarter) and sion\$h and pecvd and (optical adj index)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:15
-	0	(semiconductor adj laser) and facet and (reflection adj coating) and (thickness adj3 quarter) and sion\$h and pecvd and (optical adj index)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:16
-	0	(semiconductor adj laser) and facet and (reflection adj coating) and (thickness adj3 quarter) and pecvd and (optical adj index)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:16
-	0	(semiconductor adj laser) and facet and (reflection adj coating) and (thickness adj3 quarter) and pecvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:16
-	0	laser and facet and (anti\$reflection adj coating) and (thickness adj3 quarter) and sion\$h and pecvd and (optical adj index)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:17
-	6	(semiconductor adj laser) and facet and (reflection adj coating) and (thickness adj3 quarter)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:29
-	0	(semiconductor adj laser) and (reflection adj coating) and ((pecvd) or (plasma adj enhanced)) and sixoynh	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:30
-	0	(semiconductor adj laser) and (reflection adj coating) and ((pecvd) or (plasma adj enhanced)) and sixoyny	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:30
-	0	(semiconductor adj laser) and (reflection adj coating) and ((pecvd) or (plasma adj enhanced)) and sion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:31
-	13	(semiconductor adj laser) and (reflection adj coating) and ((pecvd) or (plasma adj enhanced))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 16:28
-	0	(semiconductor adj laser) and (reflection adj coating) and ((pecvd) or (plasma adj enhanced))and (optical adj index)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 15:32
-	4	silicon near3 oxide near nitride near3 hydrogen and reflection and coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/01 11:47

-	116	(semiconductor adj laser) and coating and (reflectiv\$3 adj3 index)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/01 11:49
-	1	(semiconductor adj laser) and coating and (reflectiv\$3 adj3 index) and 1.83	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/01 11:52
-	8	(semiconductor adj laser) and coating and (reflectiv\$3 adj3 index) and (standing adj wave)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/01 12:25
-	114	(semiconductor adj laser) and (coating adj3 index)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/01 13:20
-	65	(semiconductor adj laser) and (reflection adj coating) and (quarter adj wavelength)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/01 13:22
-	34	(semiconductor adj laser) and (reflection adj coating) and (quarter adj wavelength) and gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/01 13:22

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